

## 20V N-Channel MOSFET

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	250mΩ@4.5V	0.75A
	350mΩ@2.5V	

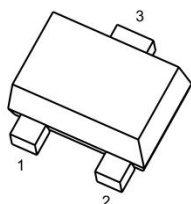
### Feature

- Surface Mount Package
- N-Channel Switch with Low  $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected:HBM 2KV

### Application

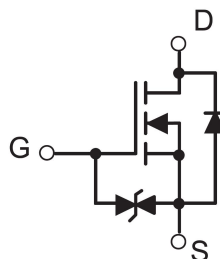
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

### Package



**SOT-723**

### Circuit diagram



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

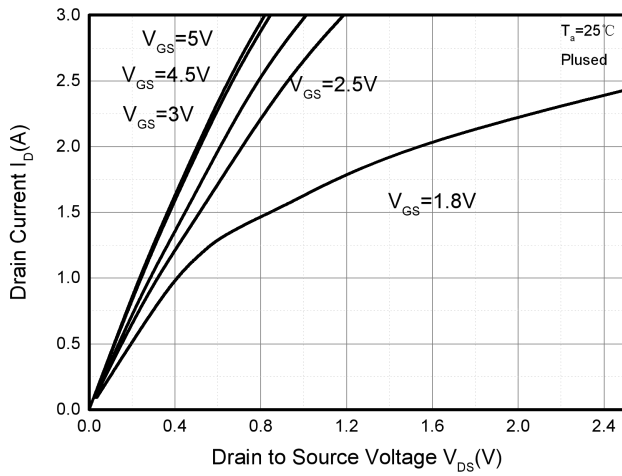
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	0.75	A
Pulsed Drain Current	$I_{DM}$	1.8	A
Power Dissipation	$P_D$	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$

**Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)**

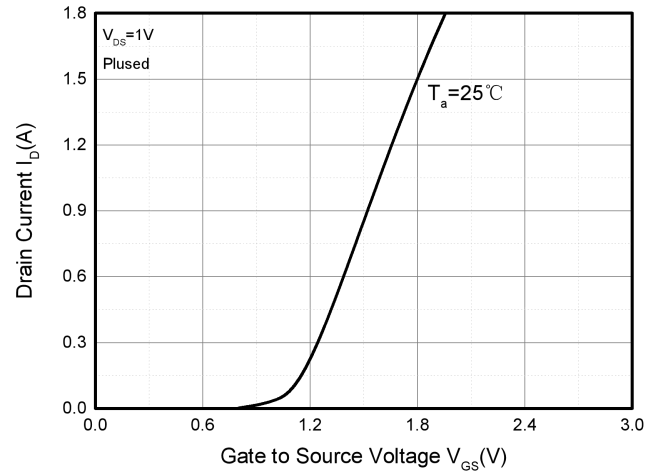
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 16V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 10$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.65	1	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 0.5A$		0.25	0.38	$\Omega$
		$V_{GS} = 2.5V, I_D = 0.5A$		0.35	0.45	
		$V_{GS} = 1.8V, I_D = 0.5A$		0.4	0.8	
Dynamic characteristics						
Input Capacitance	$C_{iss}$	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79	120	pF
Output Capacitance	$C_{oss}$			13	20	
Reverse Transfer Capacitance	$C_{rss}$			9	15	
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 500mA, R_{GEN} = 10\Omega$		6.7		ns
Turn-on rise time	$t_r$			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	$t_f$			7.4		
Source-Drain Diode characteristics						
Body Diode Voltage	$V_{SD}$	$I_S = 0.5A, V_{GS} = 0V$		0.7	1.3	V

## Typical Characteristics

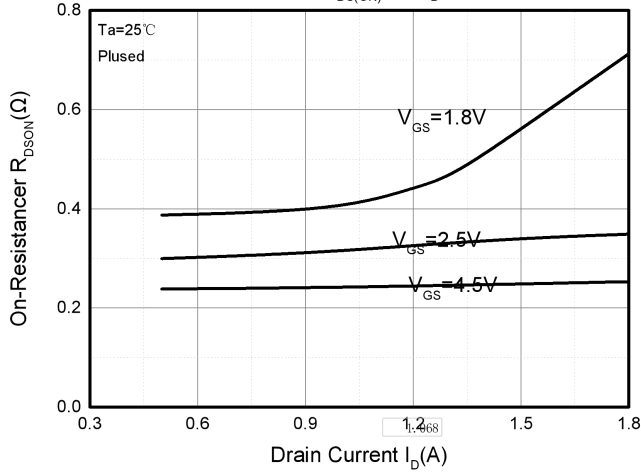
Output Characteristics



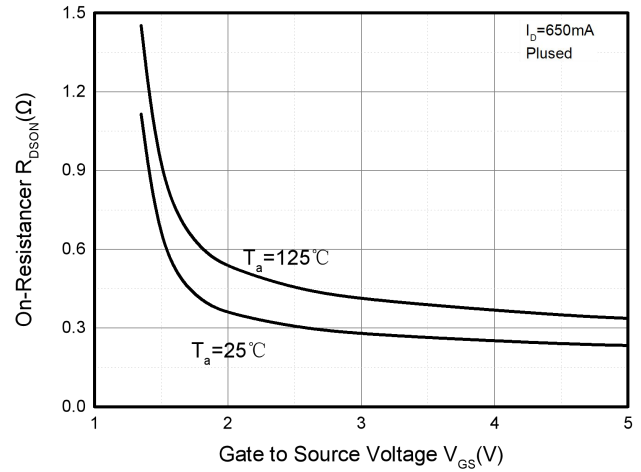
Transfer Characteristics



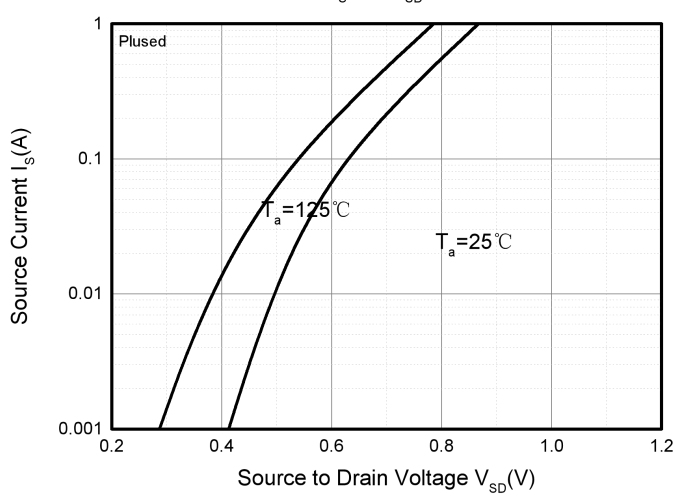
$R_{DS(ON)} - I_D$



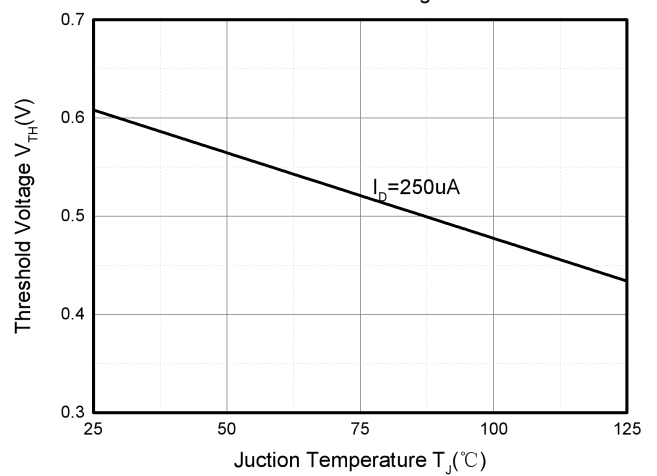
$R_{DS(ON)} - V_{GS}$

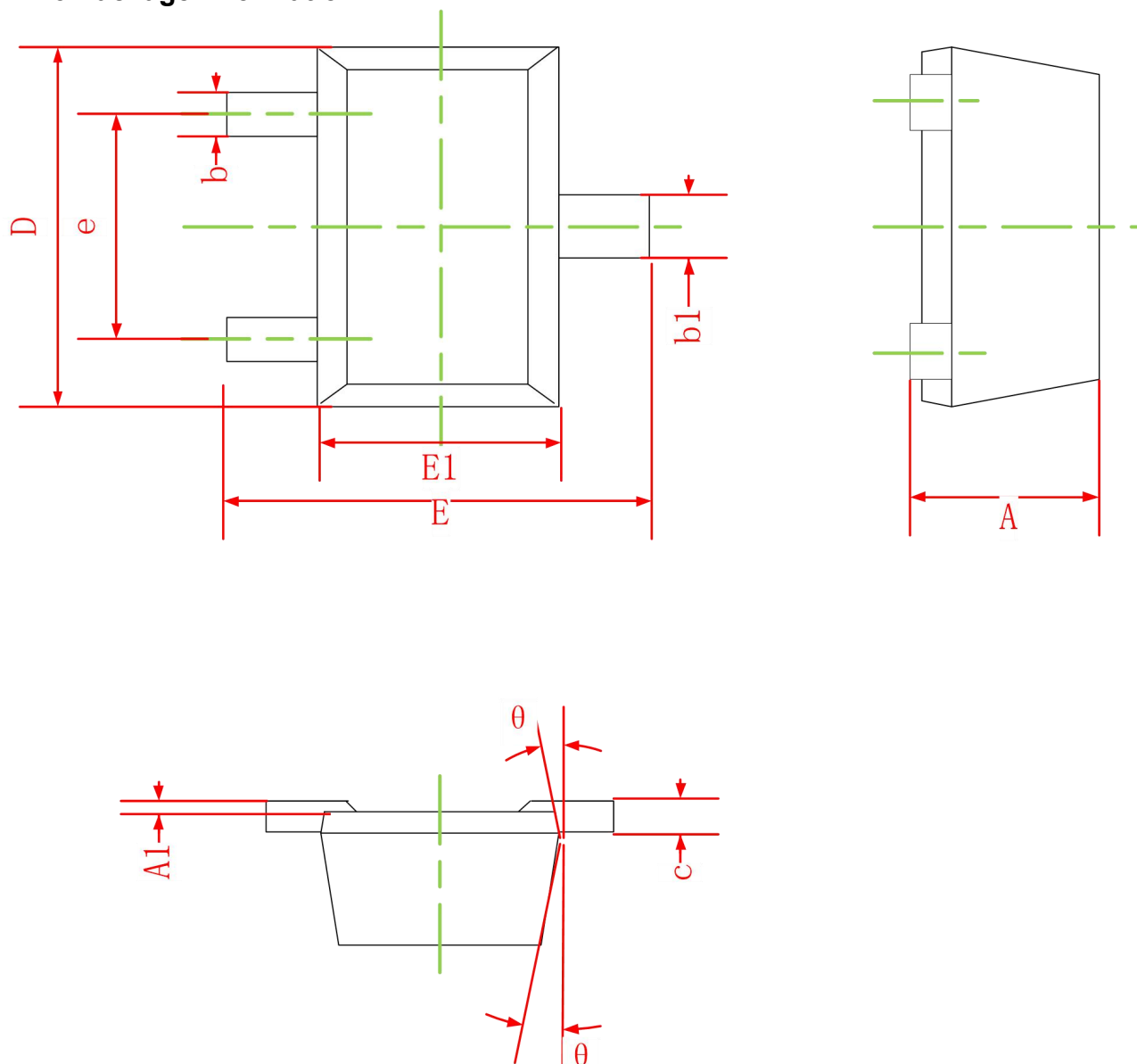


$I_S - V_{SD}$



Threshold Voltage



**SOT-723 Package Information**


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.430	0.500
A1	0.000	0.050
b	0.170	0.270
b1	0.270	0.370
c	0.080	0.150
D	1.150	1.250
E	1.150	1.250
E1	0.750	0.850
e	0.800TYP.	
$\theta$	7° REF.	